

# Kiryong Kim

## List of Publications by Year in descending order

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12  
papers

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#	ARTICLE	IF	CITATIONS
1	SRAM Write Assist Circuit Using Cell Supply Voltage Self-Collapse With Bitline Charge Sharing for Near-Threshold Operation. IEEE Transactions on Circuits and Systems II: Express Briefs, 2022, 69, 1567-1571.	3.0	1
2	SRAM Write- and Performance-Assist Cells for Reducing Interconnect Resistance Effects Increased With Technology Scaling. IEEE Journal of Solid-State Circuits, 2022, 57, 1039-1048.	5.4	5
3	A 5 Gb/s Time-Interleaved Voltage-Mode Duobinary Encoding Scheme for 3-D-Stacked IC. IEEE Journal of Solid-State Circuits, 2022, 57, 1913-1923.	5.4	2
4	A 0.166 pJ/b/pF, 3.5-5 Gb/s TSV I/O Interface With $V_{OH}$ Drift Control. IEEE Transactions on Circuits and Systems II: Express Briefs, 2021, 68, 1822-1826.	3.0	3
5	Bitline Charge Sharing Suppressed Bitline and Cell Supply Collapse Assists for Energy-efficient 6T SRAM. IEEE Access, 2021, , 1-1.	4.2	0
6	A 6.9- $\mu$ m <sup>2</sup> 3.26-ns 31.25-fJ Robust Level Shifter With Wide Voltage and Frequency Ranges. IEEE Transactions on Circuits and Systems II: Express Briefs, 2021, 68, 1433-1437.	3.0	6
7	Area- and Energy-Efficient STDP Learning Algorithm for Spiking Neural Network SoC. IEEE Access, 2020, 8, 216922-216932.	4.2	8
8	0.293-mm <sup>2</sup> Fast Transient Response Hysteretic Quasi- $V^2$ DC-DC Converter With Area-Efficient Time-Domain-Based Controller in 0.35- $\mu$ m CMOS. IEEE Journal of Solid-State Circuits, 2018, 53, 1844-1855.	5.4	17
9	Triplet-based Spike Timing Dependent Plasticity Circuit Design for three-terminal Spintronic Synapse. , 2018, , .		2
10	Thermal and solar energy harvesting boost converter with time-multiplexing MPPT algorithm. IEICE Electronics Express, 2016, 13, 20160287-20160287.	0.8	9
11	Transient Cell Supply Voltage Collapse Write Assist Using Charge Redistribution. IEEE Transactions on Circuits and Systems II: Express Briefs, 2016, 63, 964-968.	3.0	9
12	Full-Swing Local Bitline SRAM Architecture Based on the 22-nm FinFET Technology for Low-Voltage Operation. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 2016, 24, 1342-1350.	3.1	17